Abstract

Disclosed is a process for producing a solid, surface bonding between two wafer plates, of which at least one is composed of a semiconducting material, such as e.g. silicon.

The process has the following steps:

- on the cleaned surface of at least one wafer plate a film having a residual moisture from solvents containing silicates or phosphates is applied,
- the two wafer surfaces on at least one of which a film is applied are joined,
- the two wafers are tempered in the joined state at temperatures lower than approx. 420°C.

This Sheet Has Been Replaced

